

2N2326A

SILICON CONTROLLED RECTIFIER
1.6 AMP, 400 VOLT



TO-39 CASE

Central
Semiconductor Corp.

www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N2326A is a hermetically sealed silicon controlled rectifier designed for sensing circuit applications and control systems.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Forward Voltage	V_{DRM}	200	V
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
Non-Repetitive Peak Reverse Voltage	V_{RSM}	300	V
RMS On-State Current	$I_T(\text{RMS})$	1.6	A
Average On-State Current ($T_C=85^\circ\text{C}$)	$I_T(\text{AV})$	1.0	A
Peak One Cycle Surge Current ($t=8.3\text{ms}$)	I_{TSM}	15	A
Peak Gate Power Dissipation	P_{GM}	100	mW
Average Gate Power Dissipation	$P_{G(\text{AV})}$	10	mW
Peak Gate Current	I_{GM}	100	mA
Peak Gate Voltage	V_{GM}	6.0	V
Operating Junction Temperature	T_J	-65 to +125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

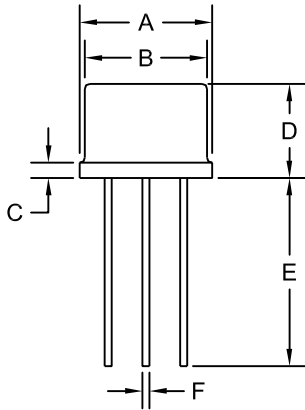
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{DRM}	$V_{DRM}=200\text{V}$, $R_{GK}=2.0\text{K}\Omega$		5.0	μA
I_{RRM}	$V_{RRM}=200\text{V}$, $R_{GK}=2.0\text{K}\Omega$		5.0	μA
I_{GT}	$V_D=6.0\text{V}$, $R_L=100\Omega$		20	μA
I_H	$V_D=6.0\text{V}$, $R_{GK}=2.0\text{K}\Omega$		2.0	mA
V_{GT}	$V_D=6.0\text{V}$, $R_L=100\Omega$		0.6	V
V_{TM}	$I_T=1.0\text{A}$, $t_p=380\mu\text{s}$		1.5	V

R0 (29-June 2016)

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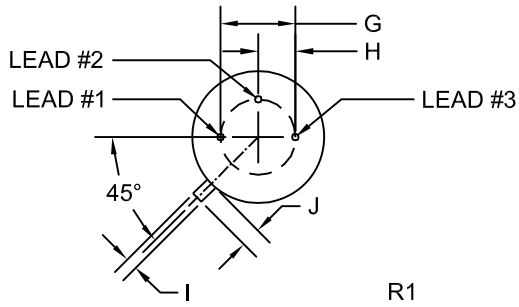


TO-39 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)



LEAD CODE:

- 1) Cathode
- 2) Gate
- 3) Anode (case)

MARKING: FULL PART NUMBER

R1

R0 (29-June 2016)